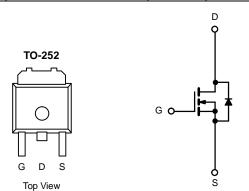


NVD20N03L27T4G-VB Datasheet

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (Ω)	I _D (A) ^{a, e}	Q _g (Typ)			
30	0.007 at V _{GS} = 10 V	70	25 nC			
	$0.009 \text{ at V}_{GS} = 4.5 \text{ V}$	60	23110			



N-Channel MOSFET

FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2011/65/EU



APPLICATIONS

- OR-ing
- Server
- DC/DC

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	30			
Gate-Source Voltage		V _{GS}	± 20	V	
	T _C = 25 °C		70		
Continuous Drain Current (T. = 175 °C)	T _C = 70 °C		50		
Continuous Drain Current (T _J = 175 °C)	T _A = 25 °C	I _D	21.8 ^{b, c}	А	
	T _A = 70 °C		18 ^{b, c}	Α	
Pulsed Drain Current	I _{DM}	200			
Avalanche Current Pulse L = 0.1 mH		I _{AS}	39		
Single Pulse Avalanche Energy	L=0.1 IIII	E _{AS}	94.8	mJ	
Continuous Source-Drain Diode Current	T _C = 25 °C	I-	50 ^{a, e}	А	
Continuous Source-Diam Diode Current	T _A = 25 °C	I _S	3.13 ^{b, c}	A	
	T _C = 25 °C		100 ^a		
Manianum Danian Dinain ation	T _C = 70 °C	P _D	75	10/	
Maximum Power Dissipation	T _A = 25 °C	r _D	3.25 ^{b, c}	W	
	T _A = 70 °C		2.33 ^{b, c}		
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Тур.	Max.	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 sec	R_{thJA}	32	40	°C/W	
Maximum Junction-to-Case	Steady State	R_{thJC}	0.5	0.6	C/VV	

Notes:

- a. Based on T_C = 25 °C.
 b. Surface mounted on 1" x 1" FR4 board.

- b. Surface in the first policy.

 c. t = 10 sec.

 d. Maximum under steady state conditions is 90 °C/W.

 e. Calculated based on maximum junction temperature. Package limitation current is 90 A.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						•
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		35		mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA		- 7.5		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.5		2.0	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zara Oata Wallana Baria Oarrad		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	90			Α
	D	V _{GS} = 10 V, I _D = 21.8 A		0.007		Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 18A$		0.009		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 21.8 A		160		S
Dynamic ^b						
Input Capacitance	C _{iss}			2201		pF
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		525		
Reverse Transfer Capacitance	C _{rss}			370		
Total Cata Charma	Qg	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 21.8 \text{ A}$	35	45		
Total Gate Charge				25	35	nC
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 21.8 \text{ A}$		15		
Gate-Drain Charge	Q _{gd}			20		
Gate Resistance	R _g	f = 1 MHz		1.4	2.1	Ω
Turn-On Delay Time	t _{d(on)}			18	27	
Rise Time	t _r	V_{DD} = 15 V, R_L = 0.625 Ω		11	17	ns
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 24$ A, V_{GEN} = 10 V, R_g = 1 Ω		70	105	
Fall Time	t _f			10	15	
Turn-On Delay Time	t _{d(on)}			55	83	
Rise Time	t _r	V_{DD} = 15 V, R_L = 0.67 Ω		180	270	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 22.5~A,~V_{GEN}$ = 4.5 V, R_g = 1 Ω		55	83	
Fall Time	t _f			12	18	
Drain-Source Body Diode Characteristic	es					
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			120	Λ
Pulse Diode Forward Current ^a	I _{SM}				120	Α
Body Diode Voltage	V_{SD}	I _S = 22 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			52	78	ns
Body Diode Reverse Recovery Charge	Q _{rr}	1 00 A di/d+ 100 A/:- T 05 00		70.2	105	nC
Reverse Recovery Fall Time	t _a	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ °C}$		27		-
Reverse Recovery Rise Time	t _b			25		ns

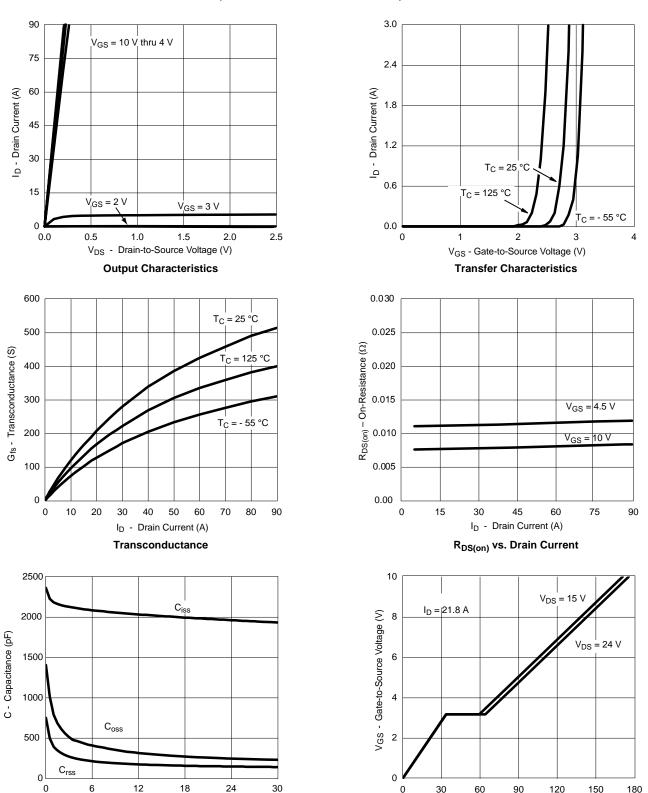
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



服务热线:400-655-8788

V_{DS} - Drain-to-Source Voltage (V) Capacitance

180

150

90

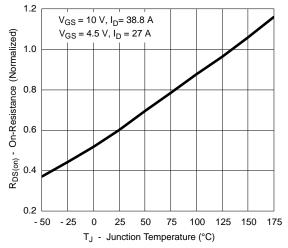
Q_g - Total Gate Charge (nC)

Gate Charge

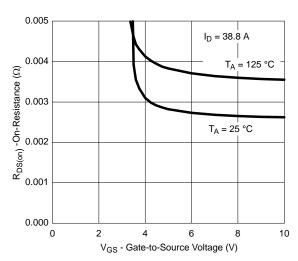
120



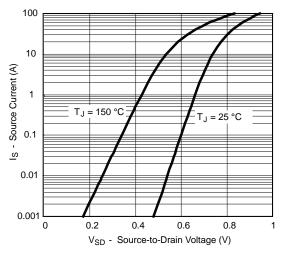
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



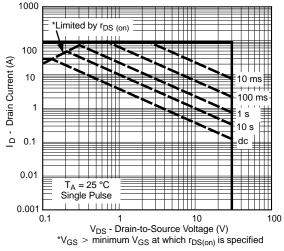
 $\rm R_{\rm DS(on)}$ vs. $\rm V_{\rm GS}$ vs. Temperature



Forward Diode Voltage vs. Temperature



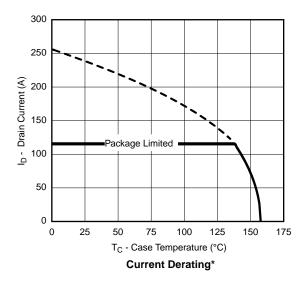
Threshold Voltage

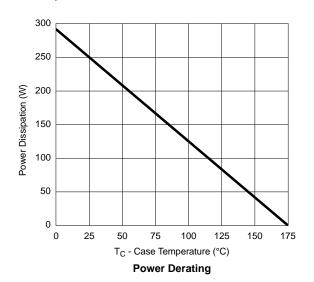


Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





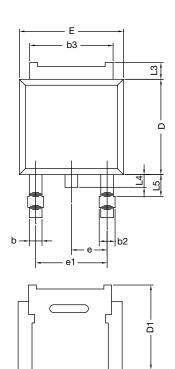
*The power dissipation P_D is based on $T_{J(max)}$ = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

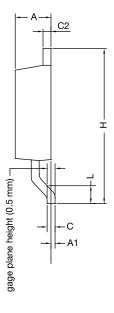


Normalized Thermal Transient Impedance, Junction-to-Case



TO-252AA CASE OUTLINE





	MILLIMETERS		TERS INCHES			
DIM.	MIN.	MAX.	MIN.	MAX.		
Α	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	5.21	-	0.205	-		
Е	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28	2.28 BSC		BSC		
e1	4.56 BSC		0.180 BSC			
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.14	1.52	0.045	0.060		
ECN: X12-0247-Rev. M, 24-Dec-12						

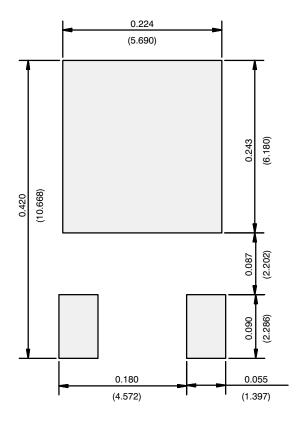
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)



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